



# BUK9515-100A

## N-channel TrenchMOS logic level FET

Rev. 3 — 19 April 2011

Product data sheet

## 1. Product profile

### 1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

### 1.2 Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance

### 1.3 Applications

- Automotive and general purpose power switching

### 1.4 Quick reference data

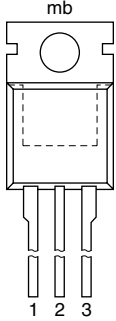
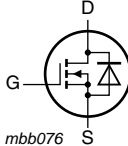
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}$	-	-	100	V
$I_D$	drain current	$T_{mb} = 25\text{ °C}$	-	-	75	A
$P_{tot}$	total power dissipation		-	-	230	W
$T_j$	junction temperature		-55	-	175	°C
<b>Static characteristics</b>						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 25\text{ A}; T_j = 25\text{ °C}$	-	11.5	14.4	mΩ
		$V_{GS} = 5\text{ V}; I_D = 25\text{ A}; T_j = 25\text{ °C}$	-	12	15	mΩ
<b>Avalanche ruggedness</b>						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 35\text{ A}; V_{sup} \leq 25\text{ V}; R_{GS} = 50\text{ }\Omega; V_{GS} = 5\text{ V}; T_{j(init)} = 25\text{ °C}; \text{unclamped}$	-	-	120	mJ



## 2. Pinning information

**Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain		
3	S	source		
mb	D	mounting base; connected to drain		

**SOT78A (TO-220AB)**

## 3. Ordering information

**Table 3. Ordering information**

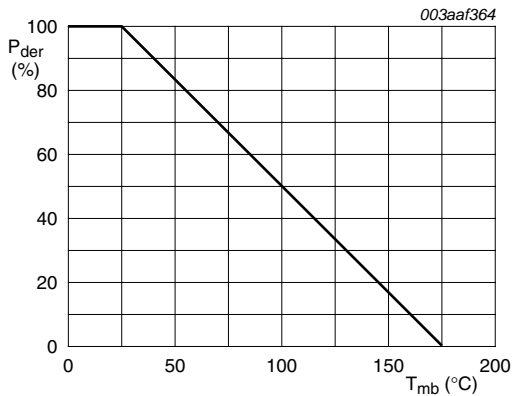
Type number	Package		
	Name	Description	Version
BUK9515-100A	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78A

## 4. Limiting values

**Table 4. Limiting values**

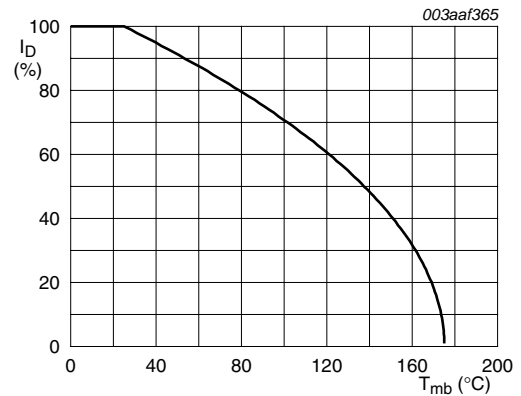
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}$	-	100	V
$V_{DGR}$	drain-gate voltage	$R_{GS} = 20\text{ k}\Omega$	-	100	V
$V_{GS}$	gate-source voltage		-10	10	V
$I_D$	drain current	$T_{mb} = 25\text{ °C}$	-	75	A
		$T_{mb} = 100\text{ °C}$	-	53	A
$I_{DM}$	peak drain current	$T_{mb} = 25\text{ °C};$ pulsed	-	313	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}$	-	230	W
$T_{stg}$	storage temperature		-55	175	°C
$T_j$	junction temperature		-55	175	°C
$V_{GSM}$	peak gate-source voltage	pulsed; $t_p \leq 50\text{ }\mu\text{s}$	-15	15	V
<b>Source-drain diode</b>					
$I_S$	source current	$T_{mb} = 25\text{ °C}$	-	75	A
$I_{SM}$	peak source current	pulsed; $T_{mb} = 25\text{ °C}$	-	313	A
<b>Avalanche ruggedness</b>					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 35\text{ A}; V_{SUP} \leq 25\text{ V}; R_{GS} = 50\text{ }\Omega;$ $V_{GS} = 5\text{ V}; T_{j(init)} = 25\text{ °C};$ unclamped	-	120	mJ



$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

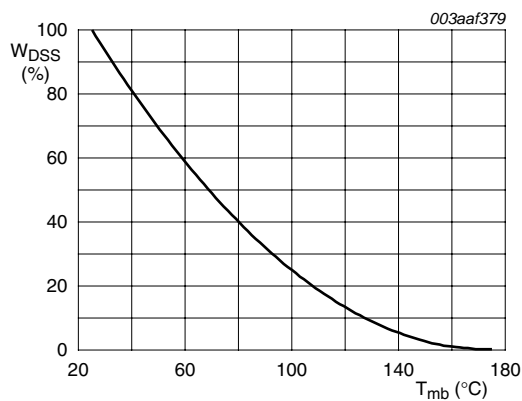
**Fig 1. Normalized total power dissipation as a function of mounting base temperature**



$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100\%$$

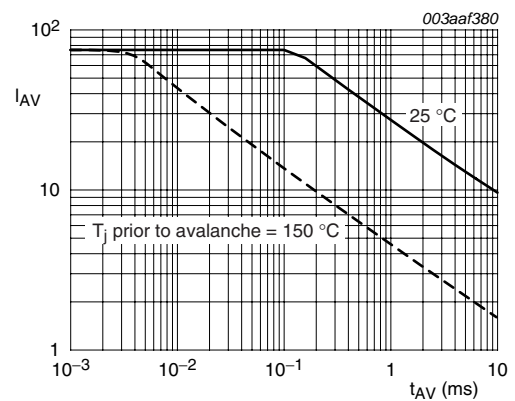
V<sub>GS</sub> ≥ 5 V

**Fig 2. Normalized continuous drain current as a function of mounting base temperature**



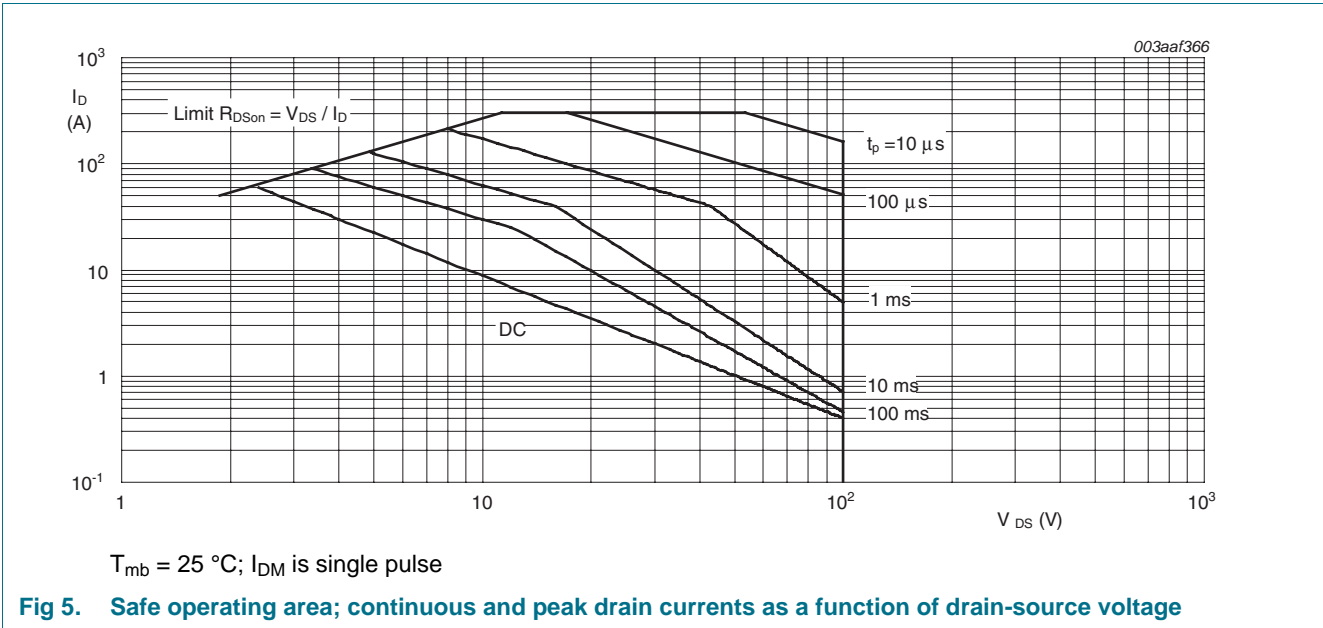
I<sub>D</sub> = 75 A

**Fig 3. Normalised drain-source non-repetitive avalanche energy as a function of mounting-base temperature**



unclamped inductive load

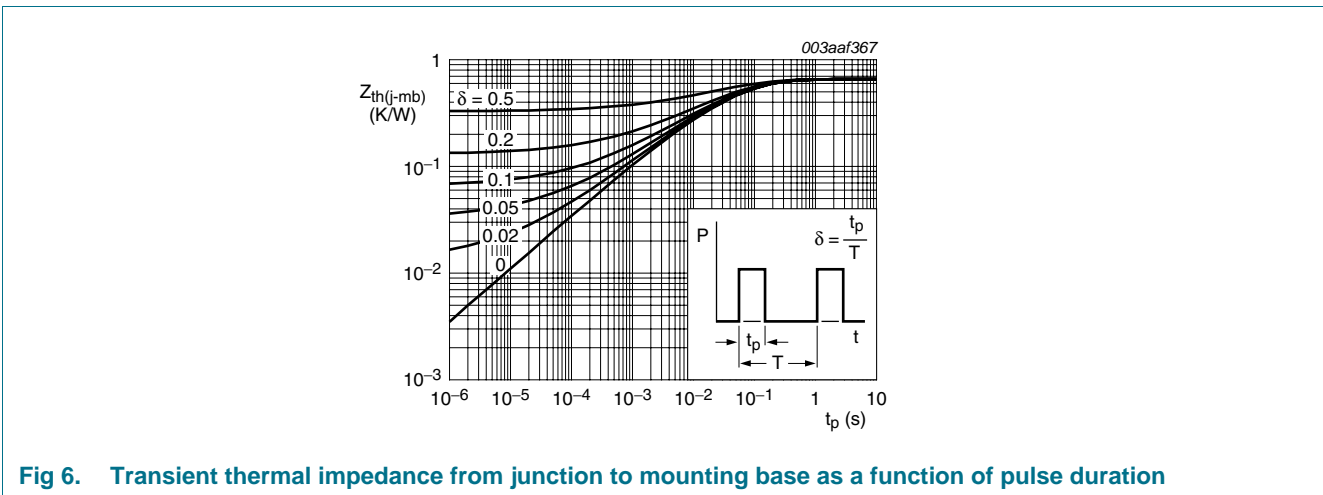
**Fig 4. Single-shot avalanche rating; avalanche current as a function of avalanche period**



## 5. Thermal characteristics

Table 5. Thermal characteristics

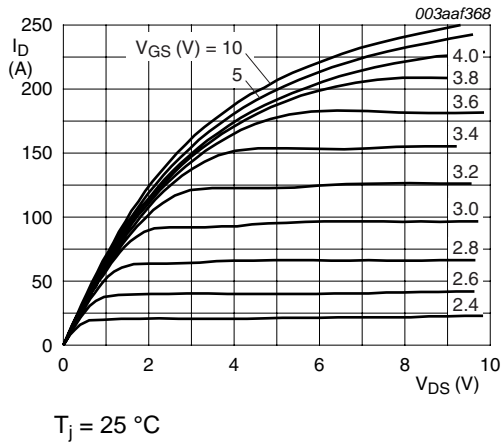
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base		-	-	0.65	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	60	-	K/W



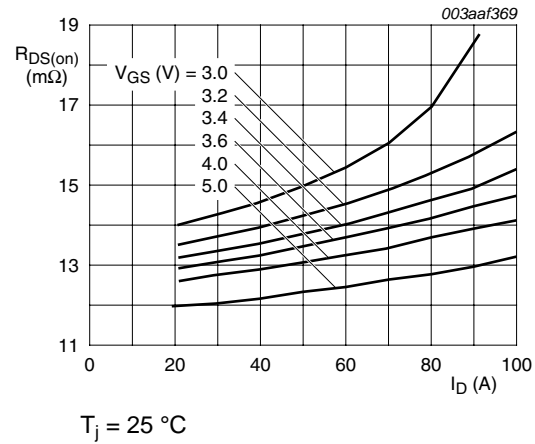
## 6. Characteristics

**Table 6. Characteristics**

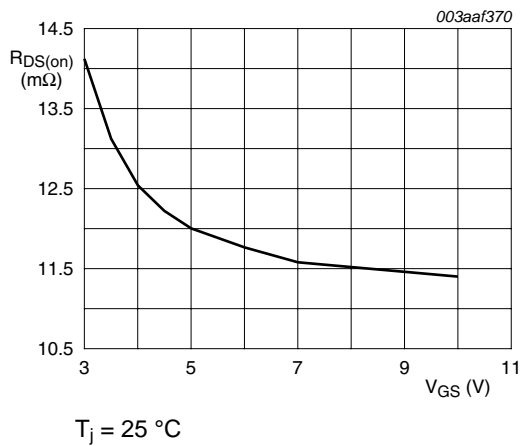
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	100	-	-	V
		$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ }^\circ\text{C}$	89	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ\text{C}$	1	1.5	2	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ\text{C}$	-	-	2.3	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ }^\circ\text{C}$	0.5	-	-	V
$I_{DSS}$	drain leakage current	$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ }^\circ\text{C}$	-	-	500	$\mu\text{A}$
		$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	0.05	10	$\mu\text{A}$
$I_{GSS}$	gate leakage current	$V_{GS} = 10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	2	100	nA
		$V_{GS} = -10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	2	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ\text{C}$	-	-	16	m $\Omega$
		$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 175 \text{ }^\circ\text{C}$	-	-	40.5	m $\Omega$
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ\text{C}$	-	11.5	14.4	m $\Omega$
		$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ\text{C}$	-	12	15	m $\Omega$
<b>Dynamic characteristics</b>						
$C_{iss}$	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz}; T_j = 25 \text{ }^\circ\text{C}$	-	6500	8600	pF
$C_{oss}$	output capacitance		-	550	660	pF
$C_{rss}$	reverse transfer capacitance		-	325	400	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 1.2 \text{ } \Omega; V_{GS} = 5 \text{ V}; R_{G(ext)} = 10 \text{ } \Omega; T_j = 25 \text{ }^\circ\text{C}$	-	45	65	ns
$t_r$	rise time		-	130	195	ns
$t_{d(off)}$	turn-off delay time		-	400	560	ns
$t_f$	fall time		-	130	190	ns
$L_D$	internal drain inductance	measured from contact screw on mounting base to centre of die; $T_j = 25 \text{ }^\circ\text{C}$	-	3.5	-	nH
		measured from drain lead 6 mm from package to centre of die; $T_j = 25 \text{ }^\circ\text{C}$	-	4.5	-	nH
$L_S$	internal source inductance	measured from source lead to source bond pad; $T_j = 25 \text{ }^\circ\text{C}$	-	7.5	-	nH
<b>Source-drain diode</b>						
$V_{SD}$	source-drain voltage	$I_S = 75 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	1.1	-	V
		$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	0.85	1.2	V
$t_{rr}$	reverse recovery time	$I_S = 75 \text{ A}; dI_S/dt = -100 \text{ A}/\mu\text{s}; V_{GS} = -10 \text{ V}; V_{DS} = 30 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	60	-	ns
$Q_r$	recovered charge		-	0.24	-	$\mu\text{C}$



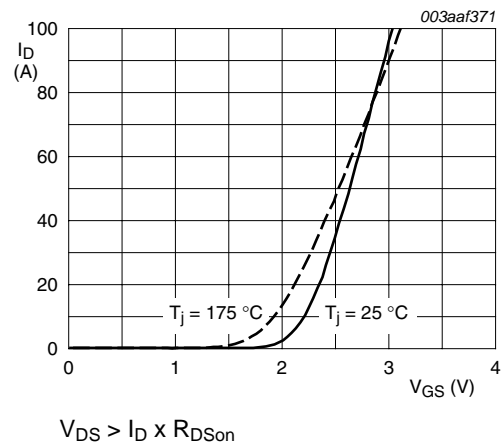
**Fig 7. Output characteristics: drain current as a function of drain-source voltage; typical values**



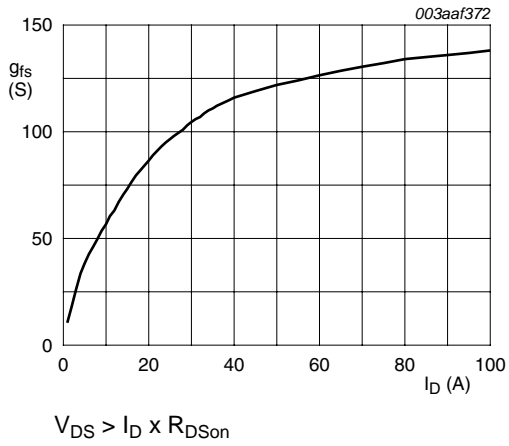
**Fig 8. Drain-source on-state resistance as a function of drain current; typical values**



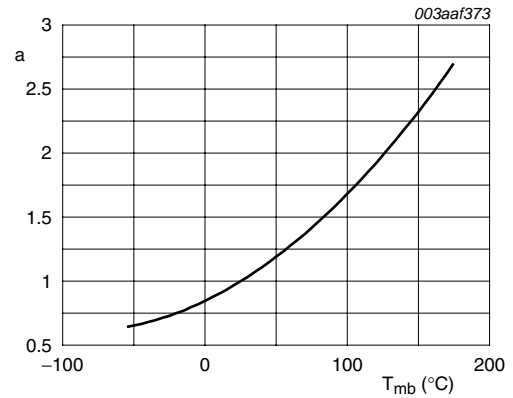
**Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values**



**Fig 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values**



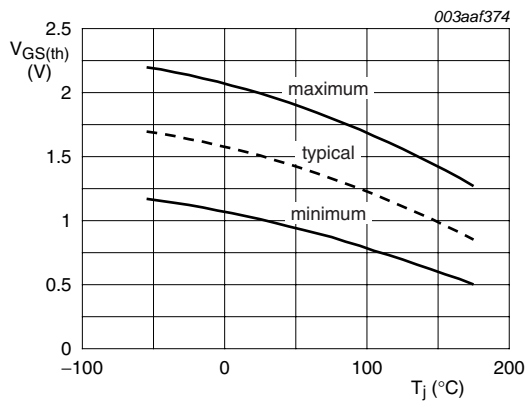
**Fig 11. Forward transconductance as a function of drain current; typical values**



$$a = \frac{R_{DSon}}{R_{DSon(25^\circ C)}}$$

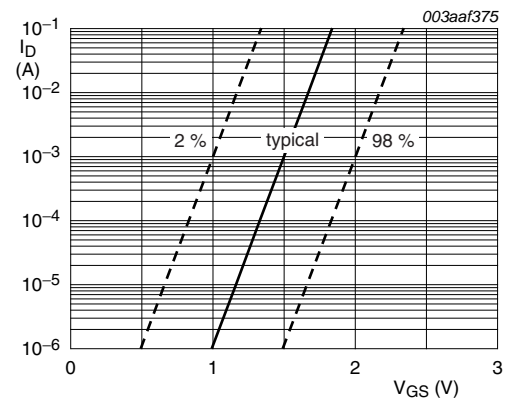
$I_D = 25 \text{ A}; V_{GS} = 5 \text{ V}$

**Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature**



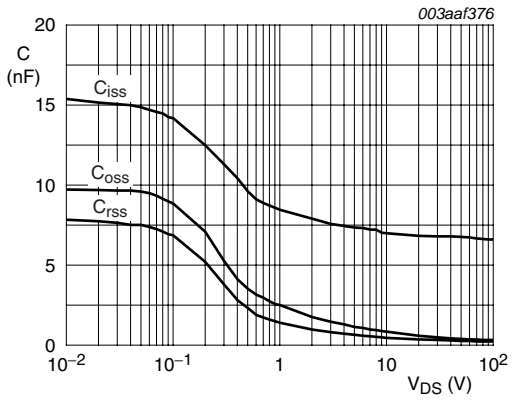
$I_D = 1 \text{ mA}; V_{DS} = V_{GS}$

**Fig 13. Gate-source threshold voltage as a function of junction temperature**



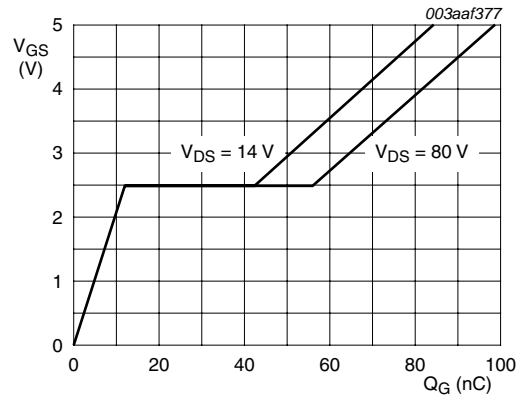
$T_j = 25 \text{ }^\circ\text{C}; V_{DS} = V_{GS}$

**Fig 14. Sub-threshold drain current as a function of gate-source voltage**



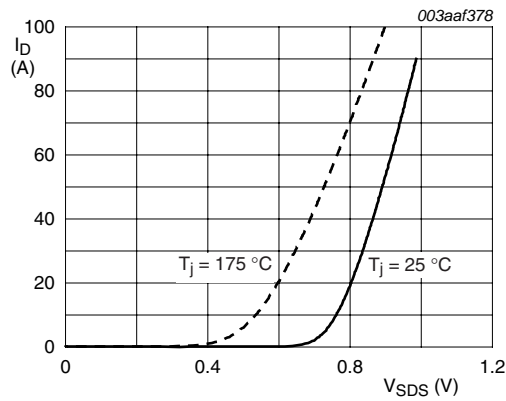
V<sub>GS</sub> = 0 V; f = 1 MHz

**Fig 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values**



T<sub>j</sub> = 25 °C; I<sub>D</sub> = 25 A

**Fig 16. Gate-source voltage as a function of gate charge; typical values**



V<sub>GS</sub> = 0 V

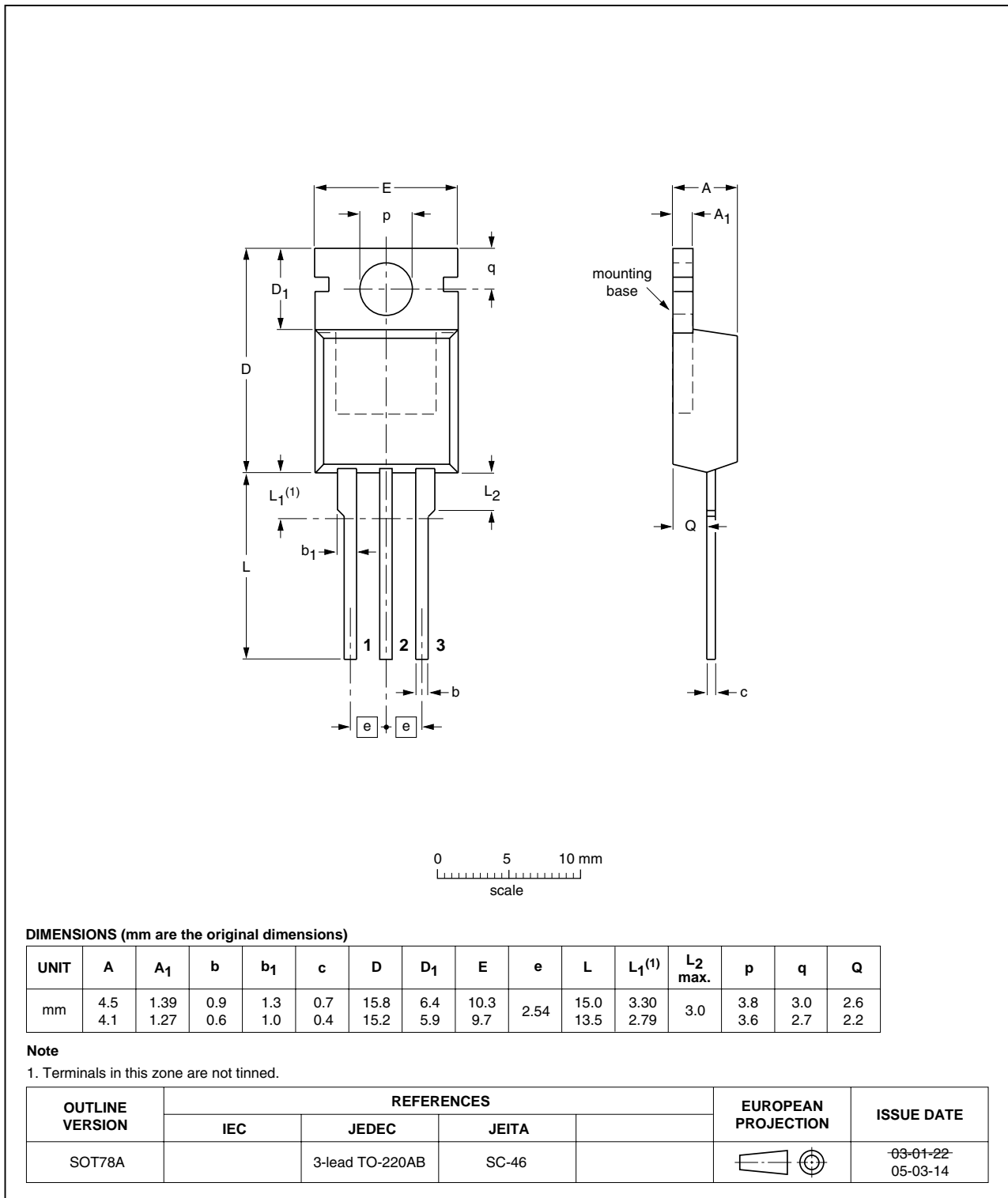
**Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values**



**7. Package outline**

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78A



**Fig 18. Package outline SOT78A (TO-220AB)**

## 8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK9515-100A v.3	20110419	Product data sheet	-	BUK9515_9615-100A_2
Modifications:		<ul style="list-style-type: none"><li>• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.</li><li>• Legal texts have been adapted to the new company name where appropriate.</li><li>• Type number BUK9515-100A separated from data sheet BUK9515_9615-100A_2.</li></ul>		
BUK9515_9615-100A_2	19991101	Product specification	-	-

## 9. Legal information

### 9.1 Data sheet status

Document status <sup>[1]</sup> <sup>[2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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